SLVS602-MARCH 2006

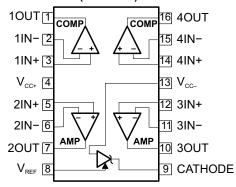
FEATURES

- OPERATIONAL AMPLIFIERS
 - Low Supply Current...200 μA/A
 - Medium Speed...2.1 MHz
 - Low-Level Output Voltage Close to V_{CC-} ...0.1 V Typ ($R_L = 10 \text{ k}\Omega$)
 - Input Common-Mode Voltage Range Includes Ground
- COMPARATORS
 - Low Supply Current...200 μA/A (V_{CC} = 5 V)
 - Input Common-Mode Voltage Range Includes Ground
 - Low Output Saturation Voltage...
 Typically 250 mV (I_{sink} = 4 mA)
- VOLTAGE REFERENCE
 - Adjustable Output Voltage...V_{REF} to 36 V
 - Sink Current Capability...1 mA to 100 mA
 - 0.4% (A Grade) and 1% (Standard Grade)
 Precision
 - Latch-Up Immunity

APPLICATIONS

- Switch-Mode Power Supplies
- Battery Chargers
- Voltage and Current Sensing
- Power-Good, Overvoltage, Undervoltage, Overcurrent Detection
- Window Comparators
- Alarms, Detectors, and Sensors

D (SOIC) OR PW (TSSOP) PACKAGE (TOP VIEW)



DESCRIPTION/ORDERING INFORMATION

The TSM102 and TMS102A combine the building blocks of a dual operational amplifier, a dual comparator, and a precision voltage reference, all of which often are used to implement a wide variety of power-management functions, including overcurrent detection, undervoltage/overvoltage detection, power-good detection, window comparators, error amplifiers, etc. Additional applications include alarm and detector/sensor applications.

The TSM102A offers a tight V_{REF} tolerance of 0.4% at 25°C. The TSM102 and TSM102A are characterized for operation from -40°C to 85°C.

ORDERING INFORMATION

T _A	MAX V _{REF} TOLERANCE (25°C)	PACK	(AGE ⁽¹⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
		SOIC - D	Tube of 75	TSM102AID	TSM102AI
	A grade: 0.4% precision	30IC - D	Reel of 2500	TSM102AIDR	1 SWI 102AI
		TSSOP – PW	Tube of 90	TSM102AIPW	SN102AI
-40°C to 85°C		1330F - FW	Reel of 2000	TSM102AIPWR	SINTUZAI
-40 C to 65 C		SOIC - D	Tube of 75	TSM102ID	TSM102I
	Standard grade:	30IC – D	Reel of 2500	TSM102IDR	131/11/021
	1% precision	TSSOP – PW	Tube of 90	TSM102IPW	SN102I
		1330F - FW	Reel of 2000	TSM102IPWR	3111021

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





Absolute Maximum Ratings(1)

over free-air temperature range (unless otherwise noted)

			MIN	MAX	TINU
V_{CC}	Supply voltage			36	V
V_{ID}	Input differential voltage			36	V
VI	Input voltage range		-0.3	36	V
I _{KA}	Voltage reference cathode current			100	mA
0	Package thermal impedance ⁽²⁾⁽³⁾	D package		73	°C/W
θ_{JA}	Package thermal impedance (27/9)	PW package		108	-C/VV
T_{J}	Maximum junction temperature			150	°C
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Recommended Operating Conditions

		MIN	MAX	UNIT
V _{CC+} - V _{CC-}	Supply voltage	3	30	V
V _{ID}	Comparator differential input voltage		V _{CC+} – V _{CC}	V
V _{KA}	Cathode-to-anode voltage	V _{REF}	36	V
I _K	Reference cathode current	1	100	mA
T _A	Operating free-air temperature	-40	85	°C

Total Device Electrical Characteristics

	PARAMETER	TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
	Total supply current,	V - 5 V V - 0 V No lood	25°C		0.8	1.5	m Λ
ICC	excluding reference cathode current	$V_{CC+} = 5 \text{ V}, V_{CC-} = 0 \text{ V}, \text{ No load}$	Full range			2	mA

⁽²⁾ Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Selecting the maximum of 150°C can affect reliability.

⁽³⁾ The package thermal impedance is calculated in accordance with JESD 51-7.



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Operational Amplifier Electrical Characteristics

 $\rm V_{CC+}$ = 5 V, $\rm V_{CC-}$ = GND, R1 connected to $\rm V_{CC}/2$ (unless otherwise noted)

	PARAMETER	TEST CONDITION	NS	T _A	MIN	TYP	MAX	UNIT
.,	lanut effect veltere			25°C		1	4.5	\/
V _{IO}	Input offset voltage			Full range			6.5	mV
αV_{IO}	Input offset voltage drift			25°C		10		μV/°C
	Input offset current			25°C		5	20	nΛ
I _{IO}	input onset current			Full range			40	nA
	Innut bigg gurrent			25°C		20	100	~ ^
I _{IB}	Input bias current			Full range			200	nA
^	Lorgo cianal valtage acia	$V_{CC+} = 30 \text{ V, R1} = 10 \text{ k}\Omega,$		25°C	50	100		V/mV
A _{VD}	Large-signal voltage gain	$V_0 = 5 \text{ V to } 25 \text{ V}$		Full range	25			V/IIIV
k _{SVR}	Supply-voltage rejection ratio	$V_{CC+} = 5 \text{ V to } 30 \text{ V}$		25°C	80	100		dB
V	Input common made voltage			25°C	V _{CC} -		V _{CC+} – 1.8	V
V _{ICM}	Input common-mode voltage			Full range	V _{CC} -		$V_{CC+} - 2.2$	V
CMRR	Common-mode rejection ratio	$V_{CC+} = 30 \text{ V},$ $V_{ICM} = 0 \text{ V to } V_{CC+} - 1.8 \text{ V}$		25°C	70	90		dB
	Short-circuit current	V 14.V V 2.5.V	Source	25°C	3	6		mA
I _{SC}	Short-circuit current	$V_{ID} = \pm 1 \text{ V}, V_{O} = 2.5 \text{ V}$	Sink	25°C	3	6		mA
.,	Lliab level output voltage	$V_{CC+} = 30 \text{ V}, R_1 = 10 \text{ k}\Omega$		25°C	27	28		V
V _{OH}	High-level output voltage	$V_{CC+} = 30 \text{ V}, R_L = 10 \text{ K}22$		Full range	26			V
V	Low level output voltage	$R_L = 10 \text{ k}\Omega$		25°C		130	170	mV
V _{OL}	Low-level output voltage	$K_L = 10 \text{ K}22$		Full range			200	IIIV
SR	Slew rate	$V_{CC} = \pm 15 \text{ V}, C_L = 100 \text{ pF}, V_I = \pm 10 \text{ V}, R_L = 10 \text{ k}\Omega$		25°C	1.3	2		V/μs
GBW	Gain bandwidth product	$R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF, f}$	= 100 kHz	25°C	1.4	2.1		MHz
Φm	Phase margin	$R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}$		25°C		45		0
THD	Total harmonic distortion			25°C		0.01		%
V _n	Equivalent input noise voltage	f = 1 kHz		25°C		19		nV/√ Hz





Comparator Electrical Characteristics

 $V_{CC+} = 5 \text{ V}, V_{CC-} = \text{GND} \text{ (unless otherwise noted)}$

	PARAMETER	TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
V	Input offeet voltage		25°C			5	mV
V _{IO}	Input offset voltage		Full range			9	mv
V _{ID}	Comparator differential input voltage		Full range			V _{CC+}	V
	Input offeet ourrent		25°C			50	nA
I _{IO}	Input offset current		Full range			150	IIA
	Input bigg gurrent		25°C			250	nA
I _{IB}	Input bias current		Full range			400	IIA
1	High-level output current	$V_{ID} = 1 \text{ V}, V_{CC} = V_{O} = 30 \text{ V}$	25°C		0.1		nA
I _{OH}	nigh-level output current	$V_{ID} = 1$ V, $V_{CC} = V_O = 30$ V	Full range			1	μΑ
V	Low-level output voltage	$V_{ID} = -1 \text{ V}, I_{sink} = 4 \text{ mA}$	25°C		250	400	mV
V _{OL}	Low-level output voltage	$V_{ID} = -1$ V , $I_{sink} = 4$ $IIIA$	Full range			700	IIIV
A _{VD}	Large-signal voltage gain	$V_{CC+} = 15 \text{ V}, \text{ R1} = 15 \text{ k}\Omega, \\ V_{O} = 1 \text{ V to } 11 \text{ V}$	25°C		200		V/mV
I _{sink}	Output sink current	$V_{O} = 1.5 \text{ V}, V_{ID} = -1 \text{ V}$	25°C	6	16		mA
V	Input common-mode		25°C	0		V _{CC+} – 1.5	V
V _{ICM}	voltage range		Full range	0		V _{CC+} – 1.5 V _{CC+} – 2	V
t _{RESP}	Response time (1)	R1 = 5.1 k Ω to V _{CC+} , V _{REF} = 1.4 V	25°C		1.3		μs
t _{RESP,large}	Large-signal response time	R1 = 5.1 k Ω to V _{CC+} , V _{REF} = 1.4 V, V _I = TTL	25°C		300		ns

⁽¹⁾ The response-time specification is for 100-mV input step with 5-mV overdrive. For larger overdrive signals, 300 ns can be obtained.



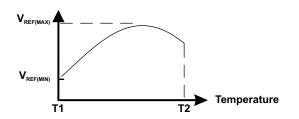
SLVS602-MARCH 2006

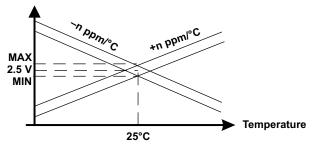
Voltage-Reference Electrical Characteristics

	PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
V	Reference voltage ⁽¹⁾	TSM102	$V_{KA} = V_{RFF}$, $I_K = 10$ mA,	25°C	2.475	2.5	2.525	V
V_{REF}	Reference voltage (1)	TSM102A	See Figure 1	25°C	2.49	2.5	2.51	V
ΔV_{REF}			$V_{KA} = V_{REF}$, $I_K = 10$ mA, See Figure 1	Full range		7	30	mV
$\frac{-V_{\text{REF}}}{T}$	Average temperature coefficient of reference input voltage ⁽²⁾		$V_{KA} = V_{REF}$, $I_K = 10 \text{ mA}$	Full range		±22	±100	ppm/°C
$\frac{V_{REF}}{V_{KA}}$	Ratio of change in reference voltage to change in cathode voltage		$V_{KA} = 3 \text{ V to } 36 \text{ V}, I_K = 10 \text{ mA},$ See Figure 2	25°C		-1.1	-2	mV/V
	Defended in the summer		$I_{K} = 10 \text{ mA}, R1 = 10 \text{ k}\Omega, R2 = \infty,$	25°C		1.5	2.5	^
I _{REF}	Reference input current		See Figure 2	Full range			3	μΑ
ΔI_{REF}	Reference input current over temperature range		I_K = 10 mA, R1 = 10 k Ω , R2 = ∞ , See Figure 2	Full range		0.5	1	μА
I _{min}	Minimum cathode curre for regulation	nt	V _{KA} = V _{REF} , See Figure 1	25°C		0.5	1	mA
I _{K,OFF}	Off-state cathode currer	nt	See Figure 3	25°C		180	500	nA

(1) ΔV_{REF} is defined as the difference between the maximum and minimum values obtained over the full temperature range. ΔV_{REF} = V_{REF(MAX)} - V_{REF(MIN)}
 (2) The temperature coefficient is defined as the slopes (positive and negative) of the voltage vs temperature limits within which the

reference voltage is specified.







PARAMETER MEASUREMENT INFORMATION

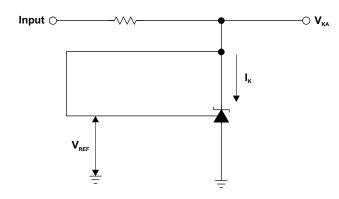


Figure 1. Test Circuit for $V_{KA} = V_{REF}$

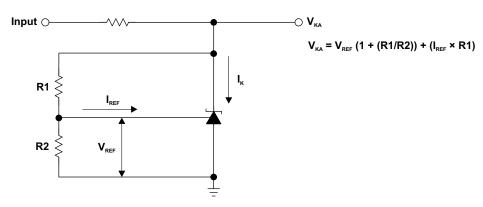


Figure 2. Test Circuit for $V_{KA} > V_{REF}$

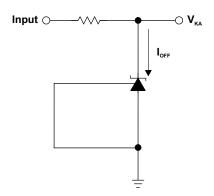
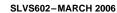


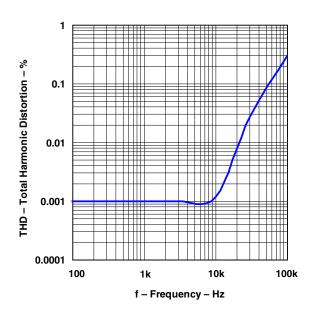
Figure 3. Test Circuit for I_{OFF}





TYPICAL CHARACTERISTICS

AMPLIFIER TOTAL HARMONIC DISTORTION VS FREQUENCY



AMPLIFIER NOISE VOLTAGE VS FREQUENCY

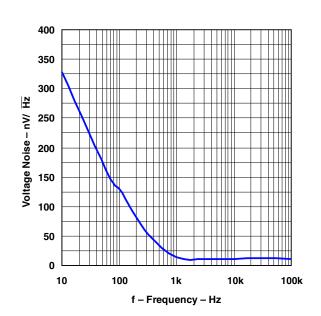


Figure 4.

GAIN AND PHASE

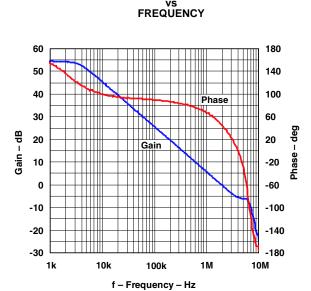


Figure 5.



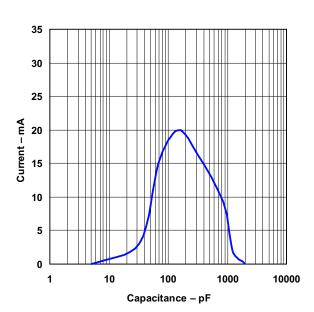
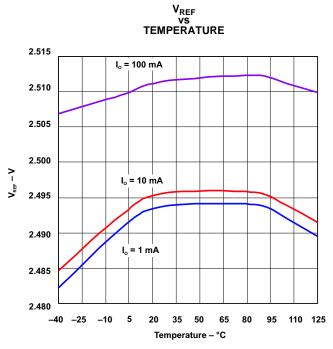


Figure 6.

Figure 7.



TYPICAL CHARACTERISTICS (continued)







10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TSM102AIDR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TSM102AI	Samples
TSM102AIPW	ACTIVE	TSSOP	PW	16	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	SN102AI	Samples
TSM102AIPWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	SN102AI	Samples
TSM102ID	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TSM102I	Samples
TSM102IDR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TSM102I	Samples
TSM102IPWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	SN102I	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

10-Dec-2020

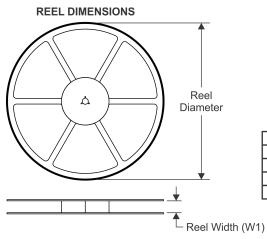
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

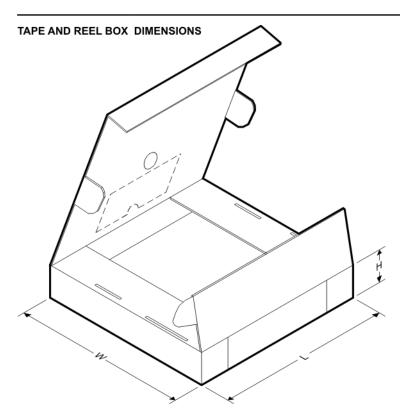
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

All difficultions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TSM102AIDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TSM102AIPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TSM102IDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TSM102IPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TSM102AIDR	SOIC	D	16	2500	853.0	449.0	35.0
TSM102AIPWR	TSSOP	PW	16	2000	853.0	449.0	35.0
TSM102IDR	SOIC	D	16	2500	853.0	449.0	35.0
TSM102IPWR	TSSOP	PW	16	2000	853.0	449.0	35.0

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Jan-2022

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TSM102AIPW	PW	TSSOP	16	90	530	10.2	3600	3.5
TSM102ID	D	SOIC	16	40	506.6	8	3940	4.32

D (R-PDS0-G16)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.





SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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